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Phase Control Thyristors (Hockey PUK Version), 1650 A



PRODUCT SUMMARY				
Package	A-24 (K-PUK)			
Diode variation	Single SCR			
I _{T(AV)}	1650 A			
V _{DRM} /V _{RRM}	1200 V, 1400 V, 1600 V, 1800 V, 2000 V			
V _{TM}	1.73 V			
I _{GT}	100 mA			
T _J	-40 °C to 125 °C			

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free RoHS

COMPLIAN

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1650	A			
I _{T(AV)}	T _{hs}	55	°C			
I _{T(RMS)}		3080	A			
	T _{hs}	25	°C			
1	50 Hz	30 500	^			
I _{TSM}	60 Hz	32 000	Α			
10.	50 Hz	4651	kA ² s			
l ² t	60 Hz	4250	KA-S			
V _{DRM} /V _{RRM}		1200 to 2000	V			
t _q	Typical	200	μs			
TJ		-40 to 125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA				
	12	1200	1300					
	14	1400	1500					
VS-ST1200CK	16	1600	1700	100				
	18	1800	1900					
	20	2000	2100					



ABSOLUTE MAXIMUM RATINGS	3					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	1	180° condu	180° conduction, half sine wave		1650 (700)	Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	3080	
		t = 10 ms	No voltage		30 500	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		32 000	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		25 700	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	26 900	
M		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	4651	
	l ² t	t = 8.3 ms			4250	
Maximum I ² t for fusing		t = 10 ms			3300	
		t = 8.3 ms	reapplied		3000	
Maximum I²√t for fusing	I ² √t	t = 0.1 ms to	t = 0.1 ms to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			ľ
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.19	11152
Maximum on-state voltage	V_{TM}	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.73	V
Maximum holding current	I _H	T 05 °C	anada ayanlı 1	O V registive lead	600	mA
Typical latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load		1000] IIIA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9	
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/μs, V_R = 50 V, dV/dt = 20 V/μs, gate 0 V 100 Ω , t_p = 500 μs	200	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA



TRIGGERING						
PARAMETER	SYMBOL		TTOT COMPLTIONS			LINUTO
PARAMETER	STWIDOL	'-	ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	1	6	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	;	3	VV
Maximum peak positive gate current	I _{GM}			3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		<u>:</u> 0	V	
Maximum peak negative gate voltage	- V _{GM}					
		T _J = -40 °C	Maximum required gate trigger/ current/voltage are the lowest	200	-	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	
		T _J = 125 °C		50	-	
		T _J = -40 °C	value which will trigger all units	1.4	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.1	3.0	V
		T _J = 125 °C		0.9	-	
DC gate current not to trigger	I _{GD}	T T	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.	25	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T_{Stg}		-40 to 150			
Maximum thermal resistance, junction to heatsink	Б	DC operation single side cooled	0.0.42			
	R _{thJ-hs}	DC operation double side cooled	0.021	K/W		
Maximum thermal resistance,	В	DC operation single side cooled	0.006	r./ vv		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500 (2500)	N (kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet A-24 (K-PUK		K-PUK)		

△R _{th} JC CONDUCTION									
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	RCONDUCTION	TEST CONDITIONS	UNITS			
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS			
180°	0.003	0.003	0.002	0.002					
120°	0.004	0.004	0.004	0.004					
90°	0.005	0.005	0.005	0.005	$T_J = T_J \text{ maximum}$	K/W			
60°	0.007	0.007	0.007	0.007					
30°	0.012	0.012	0.012	0.012					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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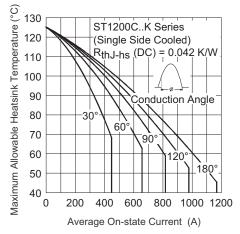


Fig. 1 - Current Ratings Characteristics

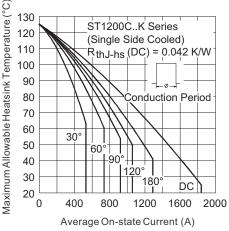


Fig. 2 - Current Ratings Characteristics

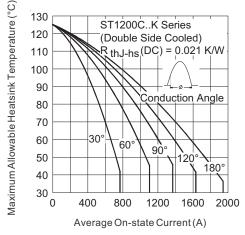


Fig. 3 - Current Ratings Characteristics

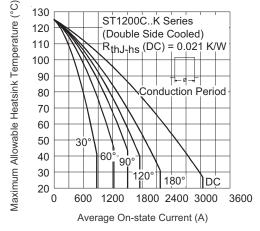


Fig. 4 - Current Ratings Characteristics

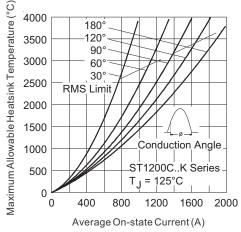


Fig. 5 - On-State Power Loss Characteristics

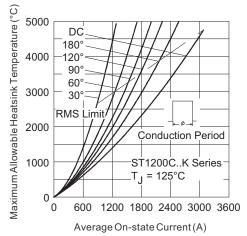
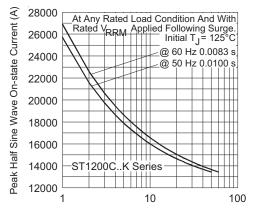


Fig. 6 - On-State Power Loss Characteristics



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Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

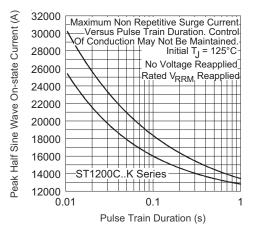


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

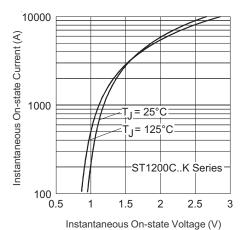


Fig. 9 - On-State Voltage Drop Characteristics

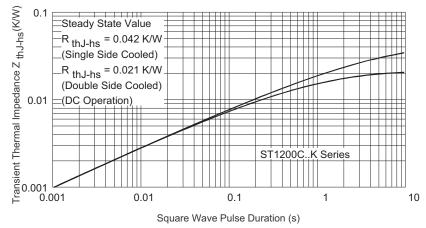


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

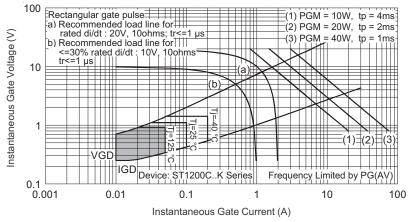
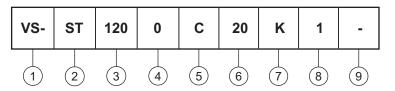


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = Converter grade

5 - C = Ceramic PUK

6 - Voltage code: Code x 100 = V_{RRM} (see Voltage Ratings table)

7 - K = PUK case A-24 (K-PUK)

8 - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

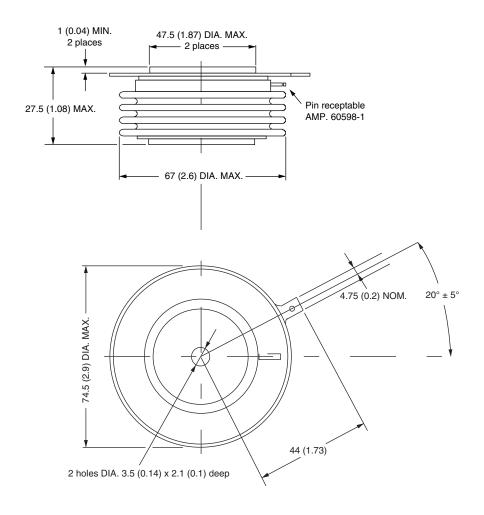
• L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

A-24 (K-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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